

Customer No.: 31561
Application No.: 10/710,765
Docket No.: 13505-US-PA

AMENDMENT

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Please amend the application as indicated hereafter.

In the Claims :

1. (original) An electrically erasable and programmable read only memory (EEPROM) cell, comprising:
 - a stacking layer disposed over a substrate, wherein the stacking layer comprises a tunneling dielectric layer, a charge trapping layer and a block dielectric layer sequentially;
 - a gate conductive layer, disposed over the stacking layer;
 - a first source/ drain region and a second source/ drain region, respectively disposed on two sides of the gate conductive layer in the substrate;
 - a first pocket implant doping region, disposed below the stacking layer in the substrate being adjacent to the first source/ drain region; and
 - a second pocket implant doping region, disposed below the stacking layer in the substrate being adjacent to the second source/ drain region, and a doping concentration of the first pocket implant doping region is different from a doping concentration of the second pocket implant doping region.
2. (original) The EEPROM cell as recited in claim 1, wherein a dopant type of the first pocket implant doping region and the second pocket implant doping region is opposite to a dopant type of the first source/ drain region and a second source/ drain region.

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3. (original) The EEPROM cell as recited in claim 2, wherein the dopant type of the first pocket implant doping region is P-type.
4. (original) The EEPROM cell as recited in claim 2, wherein the dopant type of the second pocket implant doping region is P-type.
5. (original) The EEPROM cell as recited in claim 2, wherein the dopant type of the first source/ drain region is N-type.
6. (original) The EEPROM cell as recited in claim 2, wherein the dopant type of the second source/ drain region is N-type.
7. (original) The EEPROM cell as recited in claim 1, wherein a material of the tunneling dielectric layer comprises silicon oxide.
8. (original) The EEPROM cell as recited in claim 1, wherein a material of the charge trapping layer comprises silicon nitride.
9. (original) The EEPROM cell as recited in claim 1, wherein a material of the blocking dielectric layer comprises silicon oxide.
- 10.-17. (canceled)